

NPN Epitaxial Silicon Transistor

KST10

Features

- VHF / UHF Transistor
- This is a Pb-Free Device

ABSOLUTE MAXIMUM RATINGS (Note 1)

Value are $T_A = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	30	V
V_{CEO}	Collector-Emitter Voltage	25	V
V_{EBO}	Emitter-Base Voltage	3	V
T_{STG}	Storage Temperature	150	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Refer to KSP10 for graphs.

THERMAL CHARACTERISTICS (Note 2)

Values are at $T_A = 25^\circ\text{C}$ unless otherwise noted.

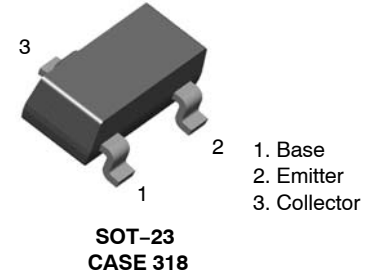
Symbol	Parameter	Max	Unit
P_D	Power dissipation	350	mW
	Derate Above 25°C	2.8	mW/ $^\circ\text{C}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	357	$^\circ\text{C}/\text{W}$

2. PCB Size: FR-4, 76 mm x 114 mm x 1.57 mm (3.0 inch x 4.5 inch x 0.062 inch) with minimum land pattern size.

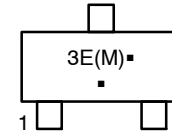
ELECTRICAL CHARACTERISTICS Values are at $T_A = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Test Condition	Min	Max	Unit
BV_{CBO}	Collector-Base Breakdown Voltage	$I_C = 100\text{ mA}, I_E = 0$	30	–	V
BV_{CEO}	Collector-Emitter Breakdown Voltage	$I_C = 1\text{ mA}, I_B = 0$	25	–	V
BV_{EBO}	Emitter-Base Breakdown Voltage	$I_E = 10\text{ mA}, I_C = 0$	3	–	V
I_{CBO}	Collector Cut-Off Current	$V_{CB} = 25\text{ V}, I_E = 0$	–	100	nA
I_{EBO}	Emitter Cut-Off Current	$V_{EB} = 2\text{ V}, I_C = 0$	–	100	nA
h_{FE}	DC Current Gain	$V_{CE} = 10\text{ V}, I_C = 4\text{ mA}$	60	–	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 4\text{ mA}, I_B = 0.4\text{ mA}$	–	0.5	V
$V_{BE(on)}$	Base-Emitter On Voltage	$V_{CE} = 10\text{ V}, I_C = 4\text{ mA}$	–	0.95	V
f_T	Current Gain Bandwidth Product	$V_{CE} = 10\text{ V}, I_C = 4\text{ mA}, f = 100\text{ MHz}$	650	–	MHz
C_{ob}	Output Capacitance	$V_{CB} = 10\text{ V}, I_E = 0, f = 1\text{ MHz}$	–	0.7	pF
C_{rb}	Common-Base Feedback Capacitance	$V_{CB} = 10\text{ V}, I_E = 0, f = 1\text{ MHz}$	–	0.65	pF
$C_{c-rbb'}$	Collector-Base Time Constant	$V_{CB} = 10\text{ V}, I_C = 4\text{ mA}, f = 31.8\text{ MHz}$	–	9	pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.



MARKING DIAGRAM

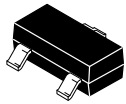


3E = Specific Device Code
M = Date Code
■ = Pb-Free Package

ORDERING INFORMATION

Device	Package	Shipping [†]
KST10MTF	SOT-23 (Pb-Free)	3000 / Tape & Reel

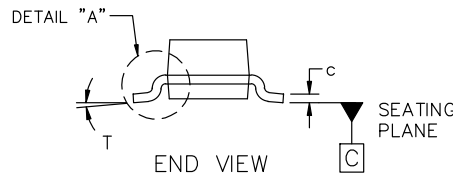
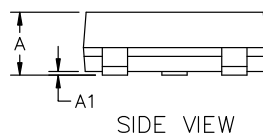
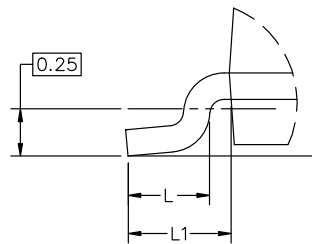
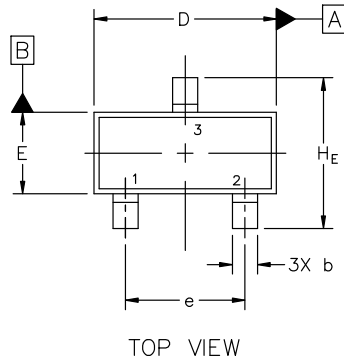
[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, [BRD8011/D](#).



SCALE 4:1

SOT-23 (TO-236) 2.90x1.30x1.00 1.90P
CASE 318
ISSUE AU

DATE 14 AUG 2024

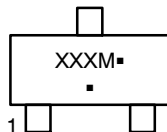


MILLIMETERS			
DIM	MIN	NOM	MAX
A	0.89	1.00	1.11
A1	0.01	0.06	0.10
b	0.37	0.44	0.50
c	0.08	0.14	0.20
D	2.80	2.90	3.04
E	1.20	1.30	1.40
e	1.78	1.90	2.04
L	0.30	0.43	0.55
L1	0.35	0.54	0.69
HE	2.10	2.40	2.64
T	0°	---	10°

NOTES:

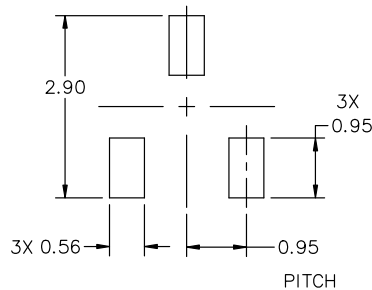
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
2. CONTROLLING DIMENSIONS: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

GENERIC
MARKING DIAGRAM*



XXX = Specific Device Code
M = Date Code
▪ = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.



RECOMMENDED
MOUNTING FOOTPRINT

* For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLES ON PAGE 2

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STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE		
STYLE 9: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 10: PIN 1. DRAIN 2. SOURCE 3. GATE	STYLE 11: PIN 1. ANODE 2. CATHODE 3. CATHODE-ANODE	STYLE 12: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 13: PIN 1. SOURCE 2. DRAIN 3. GATE	STYLE 14: PIN 1. CATHODE 2. GATE 3. ANODE
STYLE 15: PIN 1. GATE 2. CATHODE 3. ANODE	STYLE 16: PIN 1. ANODE 2. CATHODE 3. CATHODE	STYLE 17: PIN 1. NO CONNECTION 2. ANODE 3. CATHODE	STYLE 18: PIN 1. NO CONNECTION 2. CATHODE 3. ANODE	STYLE 19: PIN 1. CATHODE 2. ANODE 3. CATHODE-ANODE	STYLE 20: PIN 1. CATHODE 2. ANODE 3. GATE
STYLE 21: PIN 1. GATE 2. SOURCE 3. DRAIN	STYLE 22: PIN 1. RETURN 2. OUTPUT 3. INPUT	STYLE 23: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 24: PIN 1. GATE 2. DRAIN 3. SOURCE	STYLE 25: PIN 1. ANODE 2. CATHODE 3. GATE	STYLE 26: PIN 1. CATHODE 2. ANODE 3. NO CONNECTION
STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE				

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